

VERSION WITHOUT MARKINGS

PLEASE AMEND CLAIMS 34, 35, 37 and 38 (UNMARKED VERSION):

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Sub C1 7

34. (AMENDED) A bond pad structure, comprising:
a semiconductor substrate;
a plurality of conductive regions formed over said semiconductor substrate;
a passivating layer formed over said conductive regions, having multiple openings to each conductive region;
a barrier layer formed over said passivating layer and in said openings;
a conducting bond pad formed over each said conductive region and over said barrier layer, whereby an upper surface of said conductive bond pad provides improved adhesion for subsequently formed bonds.

35. (AMENDED) The bond pad structure of Claim 34, wherein said conducting bond pads are formed of copper.

B4 37. (AMENDED) The bond pad structure of Claim 34, wherein said conducting bond pad forms an interlocking grid array in a bond pad via contact region, which is approximately 100 by 100 microns square and the size of the structures are from about 10 to 25 microns in width, approximately 4 microns in height, and from about 4 to 10 in number, per said conducting bond pad, increasing surface area for improved adhesion.

Sub 27 38. (AMENDED) The bond pad structure of Claim 34, wherein said conducting bond pads are formed of aluminum.